STY112N65M5

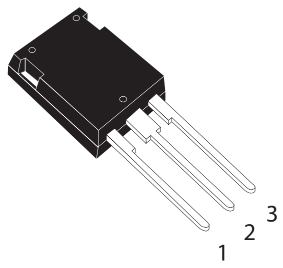
N-channel 650 V, 0.019 Ω, 96 A, MDmesh™ V Power MOSFET in Max247 package

Datasheet — production data

Features

Order code	V_{DSS} @T_{jMAX}	$R_{DS(on)}$ max	I_D
STY112N65M5	710 V	< 0.022 Ω	96 A

- Higher V_{DSS} rating
- Higher dv/dt capability
- Excellent switching performance
- Easy to drive
- 100% avalanche tested



Max247

Applications

- Switching applications

Description

This device is an N-channel MDmesh™ V Power MOSFET based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

Figure 1. Internal schematic diagram

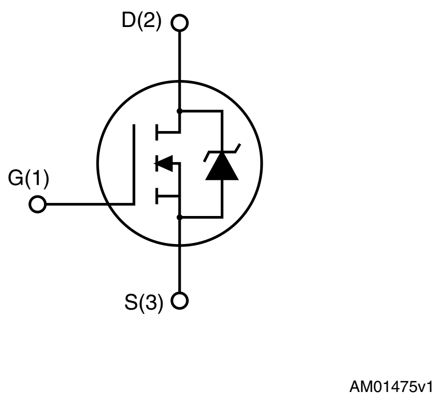


Table 1. Device summary

Order code	Marking	Package	Packaging
STY112N65M5	112N65M5	Max247	Tube

Contents

1 Electrical ratings

Table 2. **Absolute maximum ratings**

Symbol	Parameter	Value	Unit
V_{GS}	Gate- source voltage	± 25	V
I_D	Drain current (continuous) at T_C = 25 °C	96	A
I_D	Drain current (continuous) at T_C = 100 °C	61	A
I_{DM} (1)	Drain current (pulsed)	384	A
P_{TOT}	Total dissipation at T_C = 25 °C	625	W
I_{AR}	Max current during repetitive or single pulse avalanche (pulse width limited by T_{JMAX})	17	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25°C, I_D = I_{AR}, V_{DD} = 50V)	2400	mJ
dv/dt(2)	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Max. operating junction temperature	150	°C

1. Pulse width limited by safe operating area.
2. I_{SD} ≤ 96 A, di/dt = 400 A/µs, V_{DD} = 400 V, peak V_{DS} < $V_{(BR)DSS}$.

Table 3. **Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	0.2	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	30	°C/W
T_l	Maximum lead temperature for soldering purpose	300	°C

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0	650			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 650 V V_{DS} = 650 V, T_C=125 °C			10 100	µA µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 25 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10 V, I_D = 48 A		0.019	0.022	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0	-	16870 365 7	-	pF pF pF
$C_{o(tr)}$(1)	Equivalent capacitance time related	V_{GS} = 0, V_{DS} = 0 to 520 V	-	1333	-	pF
$C_{o(er)}$(2)	Equivalent capacitance energy related	V_{GS} = 0, V_{DS} = 0 to 520 V	-	350	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz open drain	-	1.26	-	Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 520 V, I_D = 48 A, V_{GS} = 10 V (see *Figure 15*)	-	350 97 118	-	nC nC nC

1. $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
2. $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(v)}$ $t_{r(v)}$ $t_{f(i)}$ $t_{c(off)}$	Voltage delay time Voltage rise time Current fall time Crossing time	V_{DD} = 400 V, I_D = 64 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 16*) (see *Figure 19*)	-	267 79 53 140	-	ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (1)	Source-drain current Source-drain current (pulsed)		-		96 384	A A
V_{SD} (2)	Forward on voltage	I_{SD} = 96 A, V_{GS} = 0	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 96 A, di/dt = 100 A/µs V_{DD} = 100 V (see *Figure 16*)	-	570 17 60		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 96 A, di/dt = 100 A/µs V_{DD} = 100 V, T_j = 150 °C (see *Figure 16*)	-	695 26 73		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

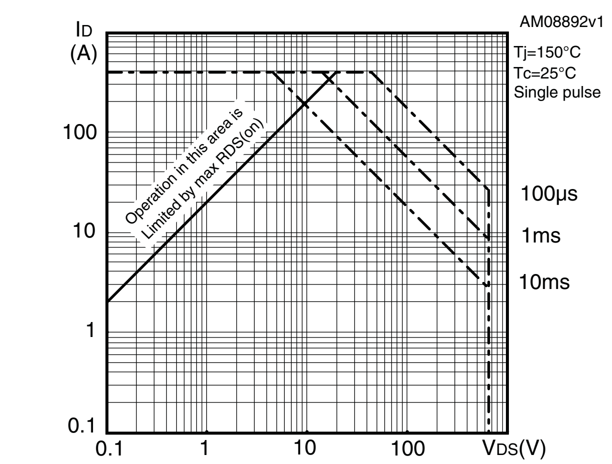


Figure 3. Thermal impedance

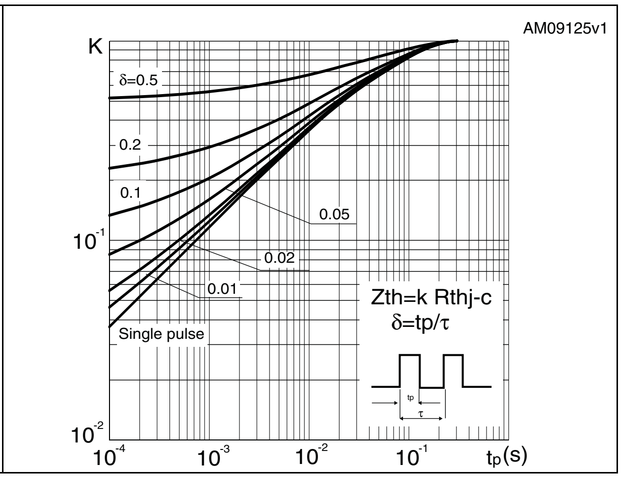


Figure 4. Output characteristics

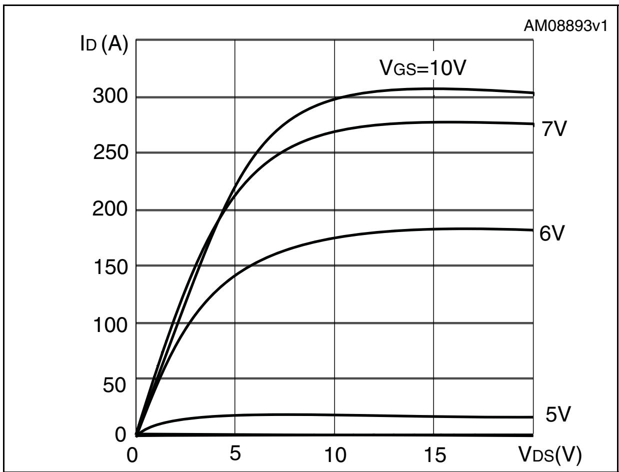


Figure 5. Transfer characteristics

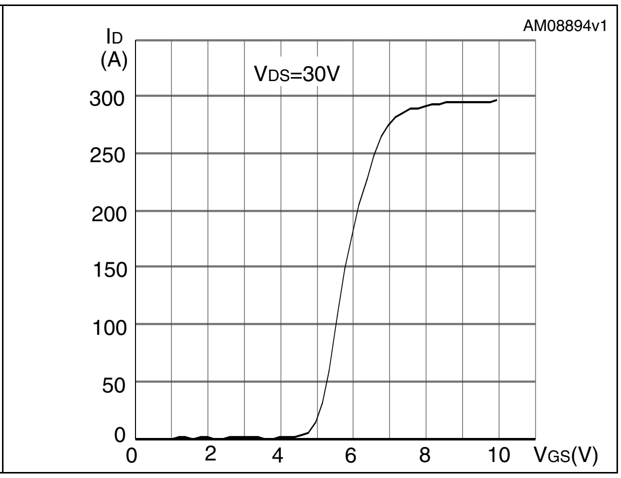


Figure 6. Normalized V_{DS} vs temperature

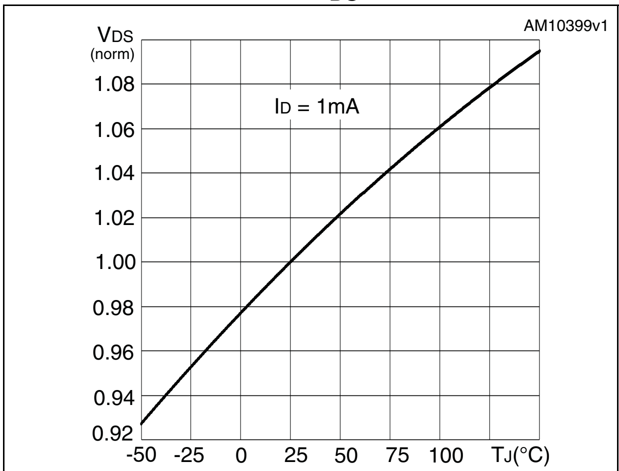


Figure 7. Static drain-source on resistance

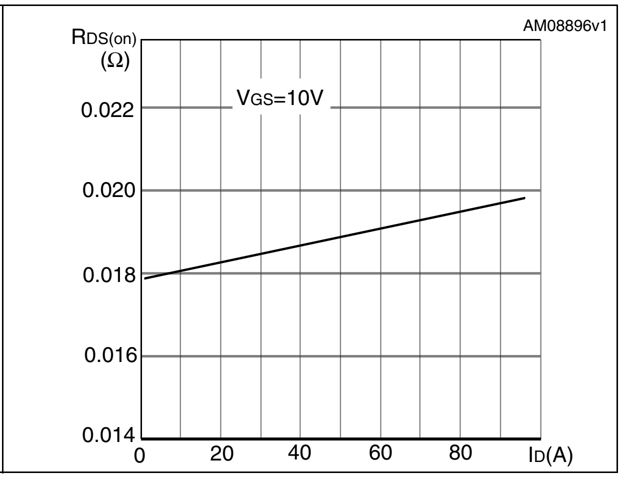


Figure 8. Gate charge vs gate-source voltage

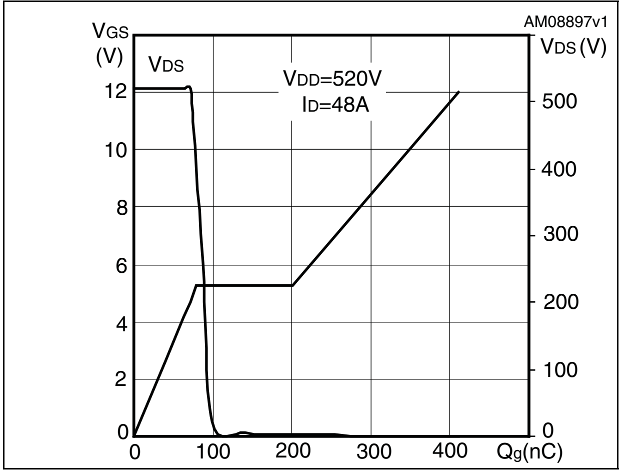


Figure 9. Capacitance variations

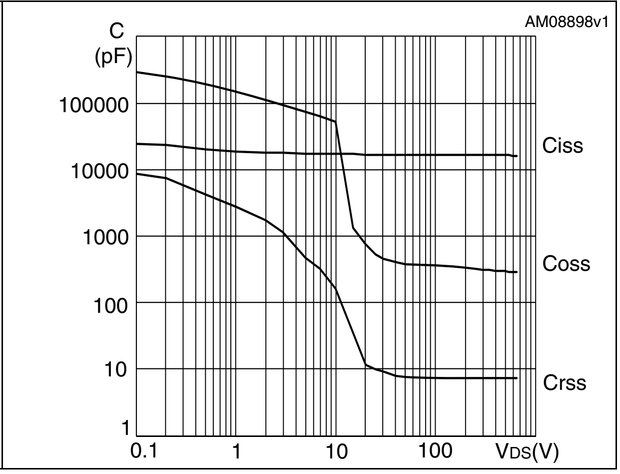


Figure 10. Normalized gate threshold voltage vs temperature

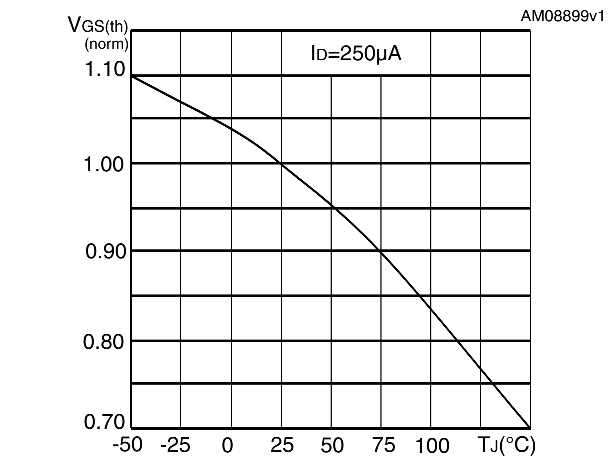


Figure 11. Normalized on resistance vs temperature

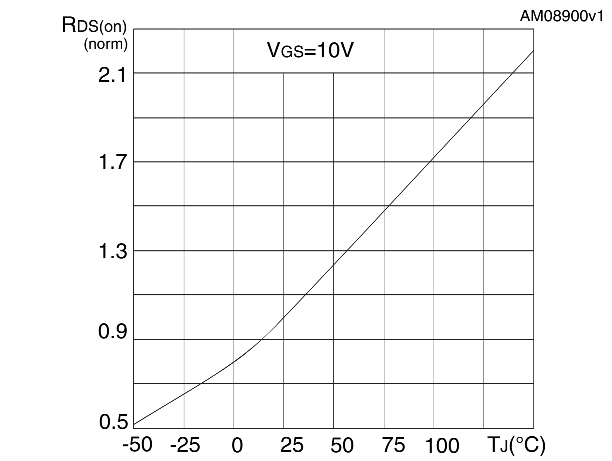


Figure 12. Output capacitance stored energy

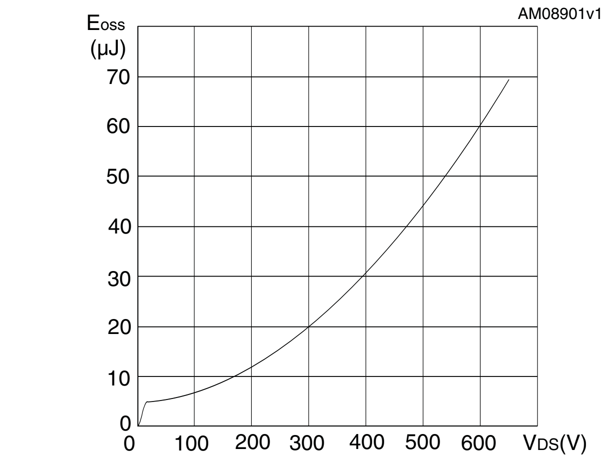
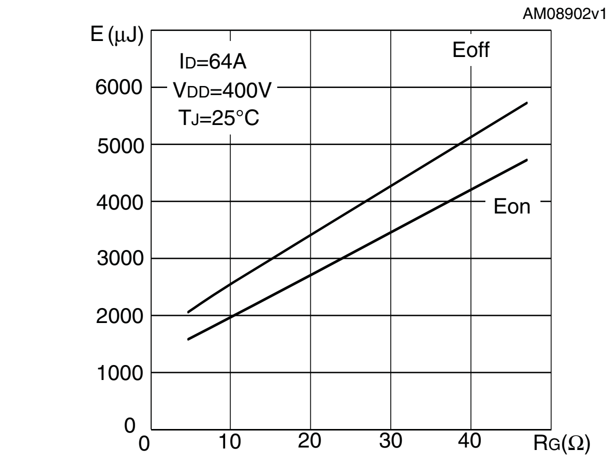


Figure 13. Switching losses vs gate resistance (1)



1. Eon including reverse recovery of a SiC diode

3 Test circuits

Figure 14. Switching times test circuit for resistive load

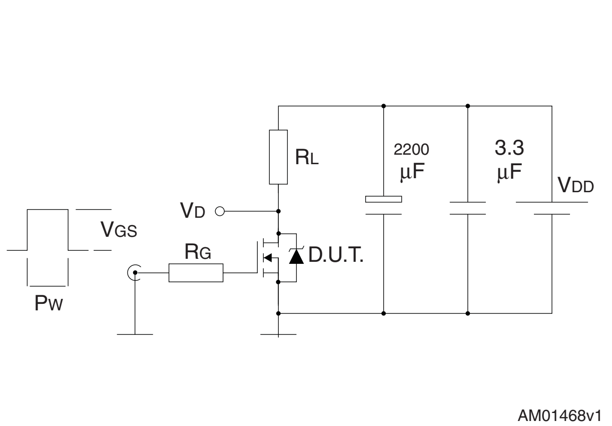


Figure 15. Gate charge test circuit

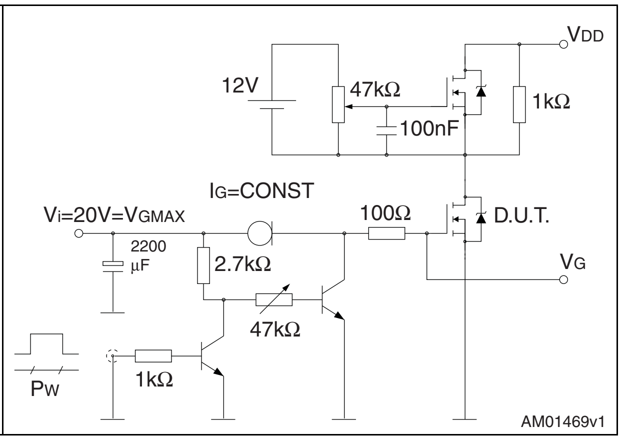


Figure 16. Test circuit for inductive load switching and diode recovery times

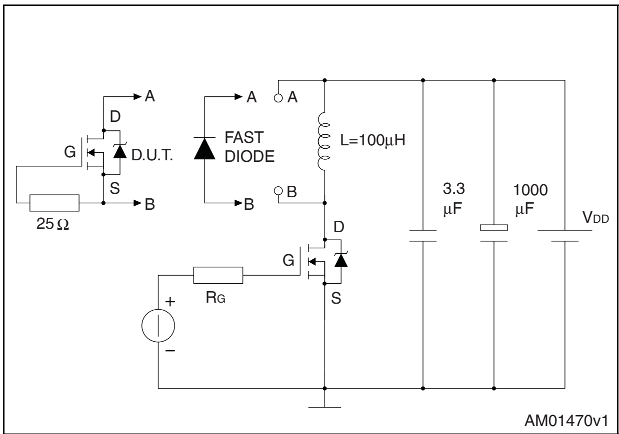


Figure 17. Unclamped inductive load test circuit

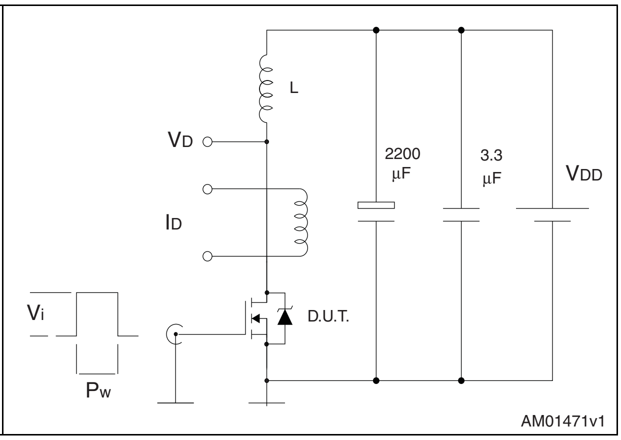


Figure 18. Unclamped inductive waveform

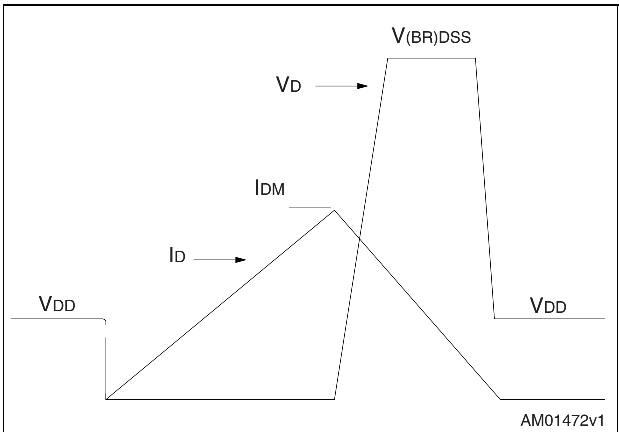
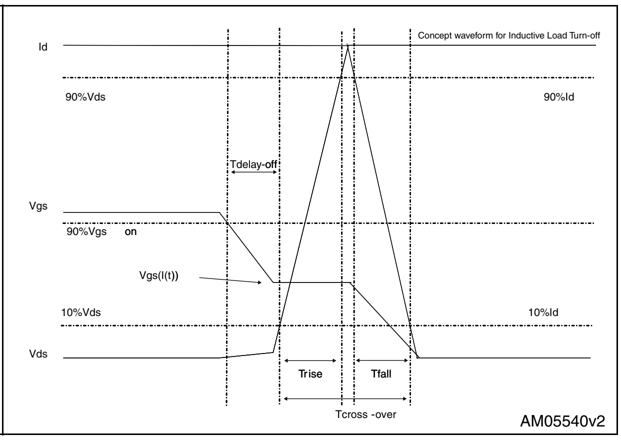


Figure 19. Switching time waveform



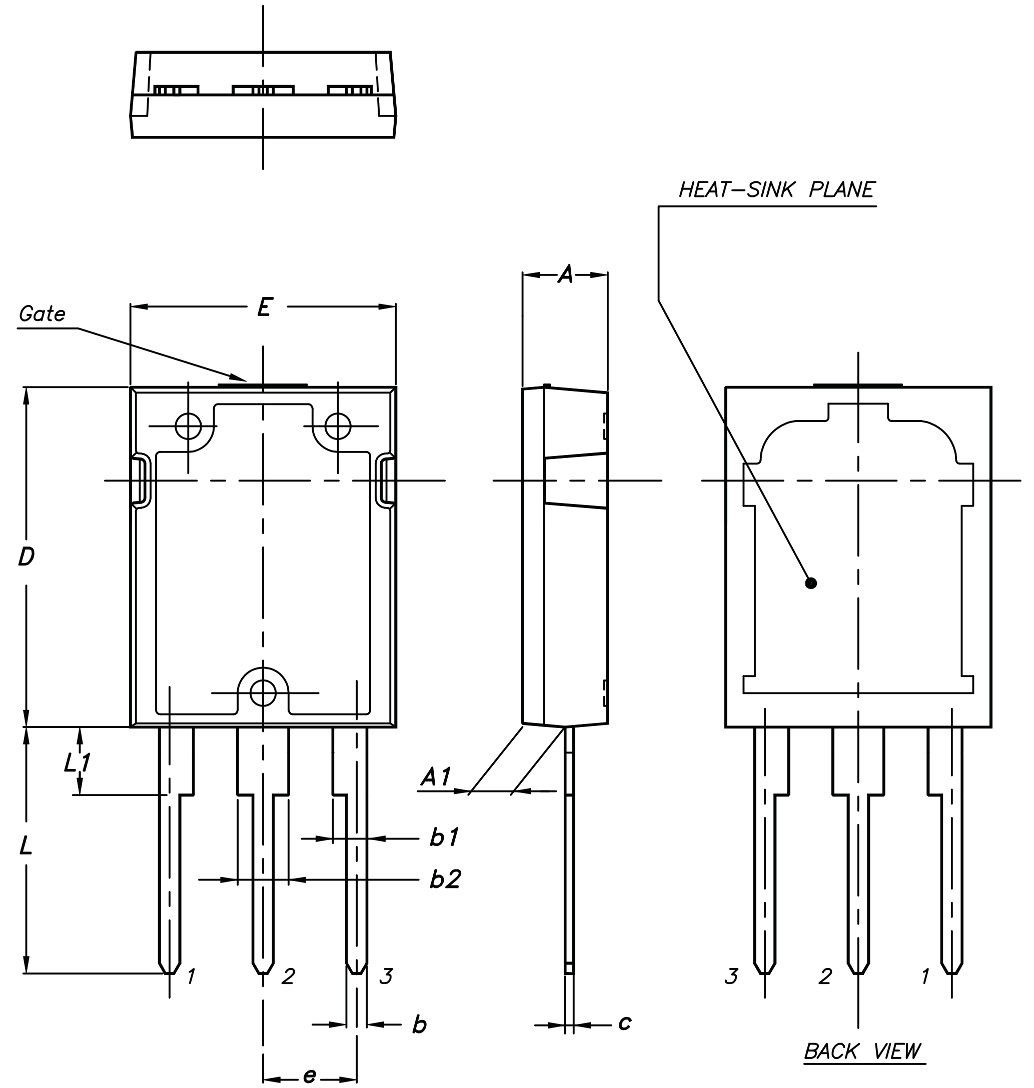
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 8. Max247 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.70		5.30
A1	2.20		2.60
b	1.00		1.40
b1	2.00		2.40
b2	3.00		3.40
c	0.40		0.80
D	19.70		20.30
e	5.35		5.55
E	15.30		15.90
L	14.20		15.20
L1	3.70		4.30

Figure 20. Max247 drawing



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
20-Jan-2009	1	First release.
20-May-2011	2	Document status pomoted from preliminary data to datasheet.
03-May-2012	3	*Section 4: Package mechanical data* has been updated.

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